

ALD LL system uses reactive chemistry to generate thin films one atomic layer at a time has a remote inductively coupled plasma source to allow for low temperature ALD depositions

Model: Cambridge Nanotech Fiji 200 with load lock



Specifications

- Type of deposition
HfO₂, Al₂O₃, TiO₂, TiN, AlN
- Type of substrate
Silicon, germanium
- Temperature for deposition
100 to 300 degrees Celsius
- Process gas used
Oxygen, Argon, Nitrogen, Ammonia

Process capabilities

- Silicon or germanium wafer of size 10mm to 6 inch can be deposited
- Multi-layer deposition can be done